

## Technische Information / technical information

IGBT-Module  
IGBT-modules

FD1200R17KE3-K\_B2

power electronics in motion  
**eupec**Vorläufige Daten  
preliminary data

## IGBT-Wechselrichter / IGBT-inverter

## Höchstzulässige Werte / maximum rated values

Kollektor-Emitter-Sperrspannung collector-emitter voltage	$T_{vj} = 25^{\circ}\text{C}$	$V_{CES}$	1700	V
Kollektor-Dauergleichstrom DC-collector current	$T_C = 80^{\circ}\text{C}$ $T_C = 25^{\circ}\text{C}$	$I_{C\text{ nom}}$ $I_C$	1200 1700	A A
Periodischer Kollektor Spitzenstrom repetitive peak collector current	$t_p = 1\text{ ms}$ , $T_C = 80^{\circ}\text{C}$	$I_{CRM}$	2400	A
Gesamt-Verlustleistung total power dissipation	$T_C = 25^{\circ}\text{C}$	$P_{tot}$	6,60	kW
Gate-Emitter-Spitzenspannung gate-emitter peak voltage		$V_{GES}$	+/-20	V

## Charakteristische Werte / characteristic values

			min.	typ.	max.	
Kollektor-Emitter Sättigungsspannung collector-emitter saturation voltage	$I_C = 1200\text{ A}$ , $V_{GE} = 15\text{ V}$ , $T_{vj} = 25^{\circ}\text{C}$ $I_C = 1200\text{ A}$ , $V_{GE} = 15\text{ V}$ , $T_{vj} = 125^{\circ}\text{C}$	$V_{CE\text{ sat}}$		2,00 2,40	2,45	V V
Gate-Schwellenspannung gate threshold voltage	$I_C = 48,0\text{ mA}$ , $V_{CE} = V_{GE}$ , $T_{vj} = 25^{\circ}\text{C}$	$V_{GEth}$	5,2	5,8	6,4	V
Gateladung gate charge	$V_{GE} = -15\text{ V} \dots +15\text{ V}$	$Q_G$		14,0		$\mu\text{C}$
Interner Gatewiderstand internal gate resistor	$T_{vj} = 25^{\circ}\text{C}$	$R_{Gint}$		1,6		$\Omega$
Eingangskapazität input capacitance	$f = 1\text{ MHz}$ , $T_{vj} = 25^{\circ}\text{C}$ , $V_{CE} = 25\text{ V}$ , $V_{GE} = 0\text{ V}$	$C_{ies}$		110		nF
Rückwirkungskapazität reverse transfer capacitance	$f = 1\text{ MHz}$ , $T_{vj} = 25^{\circ}\text{C}$ , $V_{CE} = 25\text{ V}$ , $V_{GE} = 0\text{ V}$	$C_{res}$		3,50		nF
Kollektor-Emitter Reststrom collector-emitter cut-off current	$V_{CE} = 1700\text{ V}$ , $V_{GE} = 0\text{ V}$ , $T_{vj} = 25^{\circ}\text{C}$	$I_{CES}$			5,0	mA
Gate-Emitter Reststrom gate-emitter leakage current	$V_{CE} = 0\text{ V}$ , $V_{GE} = 20\text{ V}$ , $T_{vj} = 25^{\circ}\text{C}$	$I_{GES}$			400	nA
Einschaltverzögerungszeit (ind. Last) turn-on delay time (inductive load)	$I_C = 1200\text{ A}$ , $V_{CE} = 900\text{ V}$ $V_{GE} = \pm 15\text{ V}$ , $R_{Gon} = 1,2\ \Omega$ , $T_{vj} = 25^{\circ}\text{C}$ $V_{GE} = \pm 15\text{ V}$ , $R_{Gon} = 1,2\ \Omega$ , $T_{vj} = 125^{\circ}\text{C}$	$t_{d\text{ on}}$		0,74 0,80		$\mu\text{s}$ $\mu\text{s}$
Anstiegszeit (induktive Last) rise time (inductive load)	$I_C = 1200\text{ A}$ , $V_{CE} = 900\text{ V}$ $V_{GE} = \pm 15\text{ V}$ , $R_{Gon} = 1,2\ \Omega$ , $T_{vj} = 25^{\circ}\text{C}$ $V_{GE} = \pm 15\text{ V}$ , $R_{Gon} = 1,2\ \Omega$ , $T_{vj} = 125^{\circ}\text{C}$	$t_r$		0,20 0,25		$\mu\text{s}$ $\mu\text{s}$
Abschaltverzögerungszeit (ind. Last) turn-off delay time (inductive load)	$I_C = 1200\text{ A}$ , $V_{CE} = 900\text{ V}$ $V_{GE} = \pm 15\text{ V}$ , $R_{Goff} = 1,5\ \Omega$ , $T_{vj} = 25^{\circ}\text{C}$ $V_{GE} = \pm 15\text{ V}$ , $R_{Goff} = 1,5\ \Omega$ , $T_{vj} = 125^{\circ}\text{C}$	$t_{d\text{ off}}$		1,45 1,80		$\mu\text{s}$ $\mu\text{s}$
Fallzeit (induktive Last) fall time (inductive load)	$I_C = 1200\text{ A}$ , $V_{CE} = 900\text{ V}$ $V_{GE} = \pm 15\text{ V}$ , $R_{Goff} = 1,5\ \Omega$ , $T_{vj} = 25^{\circ}\text{C}$ $V_{GE} = \pm 15\text{ V}$ , $R_{Goff} = 1,5\ \Omega$ , $T_{vj} = 125^{\circ}\text{C}$	$t_f$		0,18 0,30		$\mu\text{s}$ $\mu\text{s}$
Einschaltverlustenergie pro Puls turn-on energy loss per pulse	$I_C = 1200\text{ A}$ , $V_{CE} = 900\text{ V}$ , $L_S = 50\text{ nH}$ $V_{GE} = \pm 15\text{ V}$ , $R_{Gon} = 1,2\ \Omega$ , $T_{vj} = 25^{\circ}\text{C}$ $V_{GE} = \pm 15\text{ V}$ , $R_{Gon} = 1,2\ \Omega$ , $T_{vj} = 125^{\circ}\text{C}$	$E_{on}$		240 350		mJ mJ
Abschaltverlustenergie pro Puls turn-off energy loss per pulse	$I_C = 1200\text{ A}$ , $V_{CE} = 900\text{ V}$ , $L_S = 50\text{ nH}$ $V_{GE} = \pm 15\text{ V}$ , $R_{Goff} = 1,5\ \Omega$ , $T_{vj} = 25^{\circ}\text{C}$ $V_{GE} = \pm 15\text{ V}$ , $R_{Goff} = 1,5\ \Omega$ , $T_{vj} = 125^{\circ}\text{C}$	$E_{off}$		305 445		mJ mJ
Kurzschlußverhalten SC data	$t_p \leq 10\ \mu\text{s}$ , $V_{GE} \leq 15\text{ V}$ $T_{vj} \leq 125^{\circ}\text{C}$ , $V_{CC} = 1000\text{ V}$ , $V_{CEmax} = V_{CES} - L_{sCE} \cdot di/dt$	$I_{SC}$		4800		A
Innerer Wärmewiderstand thermal resistance, junction to case	pro IGBT per IGBT	$R_{thJC}$			19,0	K/kW
Übergangs-Wärmewiderstand thermal resistance, case to heatsink	pro IGBT / per IGBT $\lambda_{Paste} = 1\text{ W}/(\text{m}\cdot\text{K})$ / $\lambda_{grease} = 1\text{ W}/(\text{m}\cdot\text{K})$	$R_{thCH}$		23,0		K/kW

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## Diode-Wechselrichter / diode-inverter

## Höchstzulässige Werte / maximum rated values

Periodische Spitzensperrspannung repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$	$V_{RRM}$	1700	V
Dauergleichstrom DC forward current		$I_F$	1200	A
Periodischer Spitzenstrom repetitive peak forward current	$t_p = 1 \text{ ms}$	$I_{FRM}$	2400	A
Grenzlastintegral $I^2t$ - value	$V_R = 0 \text{ V}, t_p = 10 \text{ ms}, T_{vj} = 125^{\circ}\text{C}$	$I^2t$	240	$\text{kA}^2\text{s}$

## Charakteristische Werte / characteristic values

			min.	typ.	max.	
Durchlassspannung forward voltage	$I_F = 1200 \text{ A}, V_{GE} = 0 \text{ V}, T_{vj} = 25^{\circ}\text{C}$ $I_F = 1200 \text{ A}, V_{GE} = 0 \text{ V}, T_{vj} = 125^{\circ}\text{C}$	$V_F$		1,80 1,90	2,20	V V
Rückstromspitze peak reverse recovery current	$I_F = 1200 \text{ A}, -di_F/dt = 7000 \text{ A}/\mu\text{s}$ $V_R = 900 \text{ V}, V_{GE} = -15 \text{ V}, T_{vj} = 25^{\circ}\text{C}$ $V_R = 900 \text{ V}, V_{GE} = -15 \text{ V}, T_{vj} = 125^{\circ}\text{C}$	$I_{RM}$		1150 1250		A A
Sperrverzögerungsladung recovered charge	$I_F = 1200 \text{ A}, -di_F/dt = 7000 \text{ A}/\mu\text{s}$ $V_R = 900 \text{ V}, V_{GE} = -15 \text{ V}, T_{vj} = 25^{\circ}\text{C}$ $V_R = 900 \text{ V}, V_{GE} = -15 \text{ V}, T_{vj} = 125^{\circ}\text{C}$	$Q_r$		305 510		$\mu\text{C}$ $\mu\text{C}$
Abschaltenergie pro Puls reverse recovery energy	$I_F = 1200 \text{ A}, -di_F/dt = 7000 \text{ A}/\mu\text{s}$ $V_R = 900 \text{ V}, V_{GE} = -15 \text{ V}, T_{vj} = 25^{\circ}\text{C}$ $V_R = 900 \text{ V}, V_{GE} = -15 \text{ V}, T_{vj} = 125^{\circ}\text{C}$	$E_{rec}$		190 340		mJ mJ
Innerer Wärmewiderstand thermal resistance, junction to case	pro Diode per diode	$R_{thJC}$			42,0	K/kW
Übergangs-Wärmewiderstand thermal resistance, case to heatsink	pro Diode / per diode $\lambda_{\text{Paste}} = 1 \text{ W}/(\text{m}\cdot\text{K}) / \lambda_{\text{grease}} = 1 \text{ W}/(\text{m}\cdot\text{K})$	$R_{thCH}$		52,0		K/kW

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## Modul / module

Isolations-Prüfspannung insulation test voltage	RMS, f = 50 Hz, t = 1 min.	V <sub>ISOL</sub>	4,0		kV
Material Modulgrundplatte material of module baseplate			AlSiC		
Material für innere Isolation material for internal insulation			AlN		
Kriechstrecke creepage distance	Kontakt - Kühlkörper / terminal to heatsink Kontakt - Kontakt / terminal to terminal		32,2 32,2		mm
Luftstrecke clearance distance	Kontakt - Kühlkörper / terminal to heatsink Kontakt - Kontakt / terminal to terminal		19,1 19,1		mm
Vergleichszahl der Kriechwegbildung comparative tracking index		CTI	> 400		
			min.	typ.	max.
Übergangs-Wärmewiderstand thermal resistance, case to heatsink	pro Modul / per module $\lambda_{\text{Paste}} = 1 \text{ W}/(\text{m}\cdot\text{K}) / \lambda_{\text{grease}} = 1 \text{ W}/(\text{m}\cdot\text{K})$	R <sub>thCH</sub>		8,00	K/kW
Modulinduktivität stray inductance module		L <sub>sCE</sub>		25	nH
Modulleitungswiderstand, Anschlüsse - Chip module lead resistance, terminals - chip	T <sub>C</sub> = 25°C, pro Schalter / per switch	R <sub>CC'+EE'</sub> R <sub>AA'+CC'</sub>		0,37 0,37	mΩ
Höchstzulässige Sperrschichttemperatur maximum junction temperature		T <sub>vj max</sub>			150 °C
Temperatur im Schaltbetrieb temperature under switching conditions		T <sub>vj op</sub>	-40		125 °C
Lagertemperatur storage temperature		T <sub>stg</sub>	-40		125 °C
Anzugsdrehmoment f. mech. Befestigung mounting torque	Schraube / screw M6	M	4,25	-	5,75 Nm
Anzugsdrehmoment f. elektr. Anschlüsse terminal connection torque	Schraube / screw M4 Schraube / screw M8	M	1,8 8,0	- -	2,1 10 Nm
Gewicht weight		G		1050	g

**Mit dieser technischen Information werden Halbleiterbauelemente spezifiziert, jedoch keine Eigenschaften zugesichert. Sie gilt in Verbindung mit den zugehörigen technischen Erläuterungen.**

**This technical information specifies semiconductor devices but guarantees no characteristics. It is valid with the appropriate technical explanations.**

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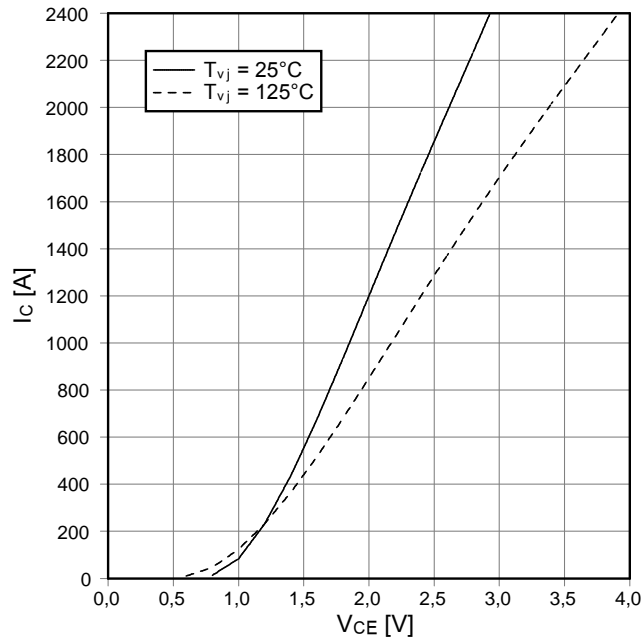
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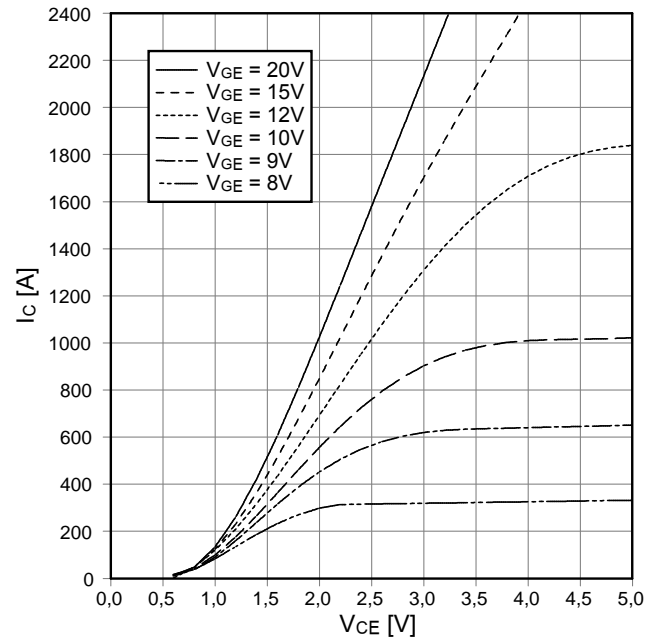


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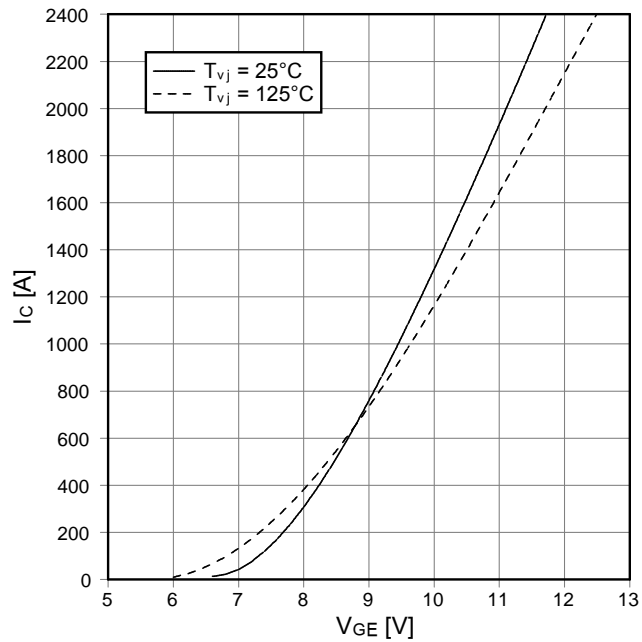
Ausgangskennlinie IGBT-Wechselr. (typisch)  
output characteristic IGBT-inverter (typical)  
 $I_c = f(V_{CE})$   
 $V_{GE} = 15\text{ V}$



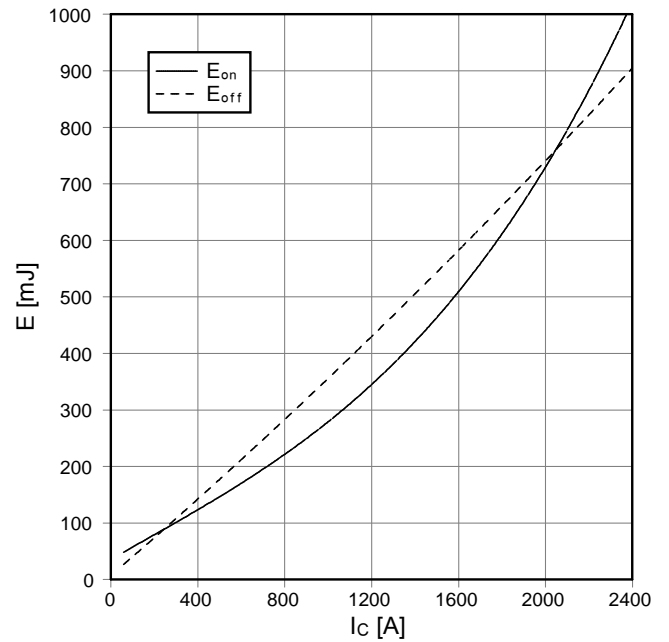
Ausgangskennlinienfeld IGBT-Wechselr. (typisch)  
output characteristic IGBT-inverter (typical)  
 $I_c = f(V_{CE})$   
 $T_{vj} = 125^\circ\text{C}$



Übertragungscharakteristik IGBT-Wechselr. (typisch)  
transfer characteristic IGBT-inverter (typical)  
 $I_c = f(V_{GE})$   
 $V_{CE} = 20\text{ V}$



Schaltverluste IGBT-Wechselr. (typisch)  
switching losses IGBT-inverter (typical)  
 $E_{on} = f(I_c), E_{off} = f(I_c)$   
 $V_{GE} = \pm 15\text{ V}, R_{Gon} = 1,2\ \Omega, R_{Goff} = 1,5\ \Omega, V_{CE} = 900\text{ V},$   
 $T_{vj} = 125^\circ\text{C}$



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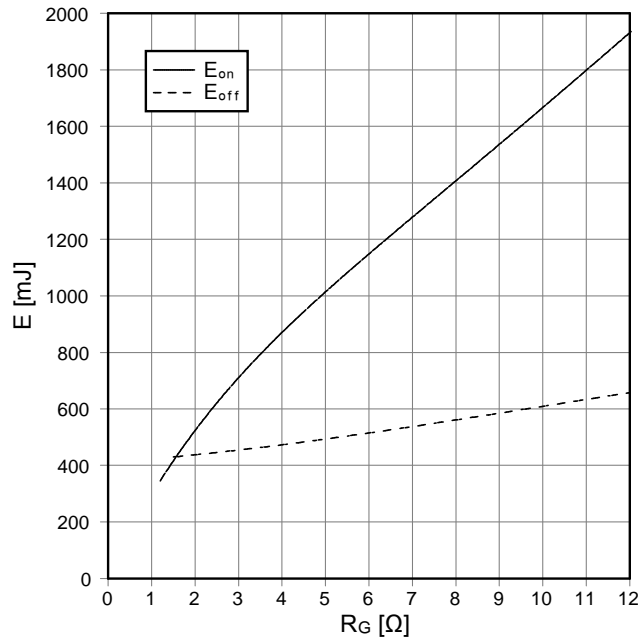
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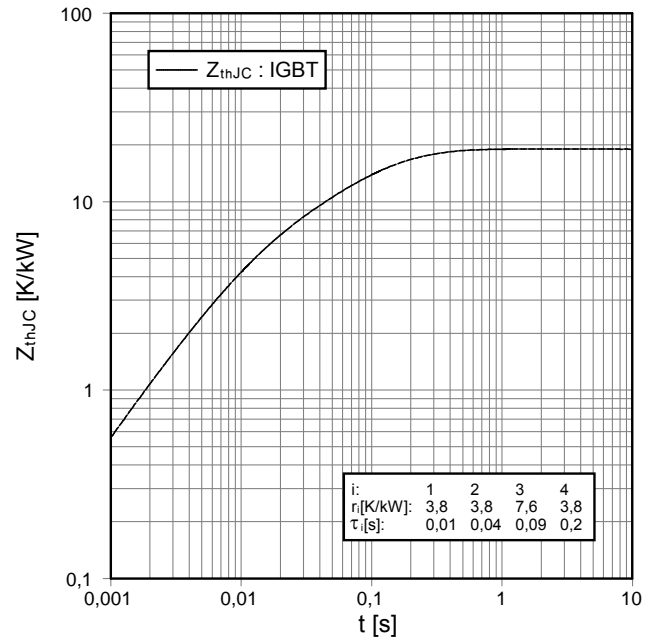


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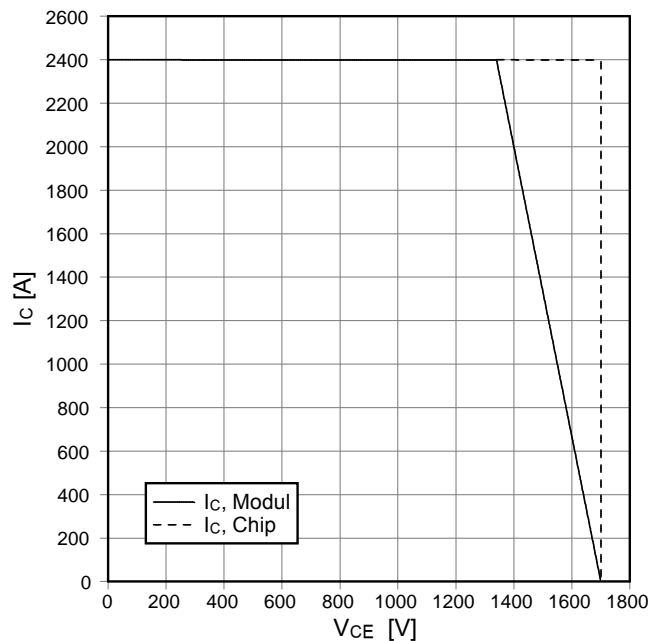
Schaltverluste IGBT-Wechsel. (typisch)  
switching losses IGBT-inverter (typical)  
 $E_{on} = f(R_G)$ ,  $E_{off} = f(R_G)$   
 $V_{GE} = \pm 15\text{ V}$ ,  $I_C = 1200\text{ A}$ ,  $V_{CE} = 900\text{ V}$ ,  $T_{vj} = 125^\circ\text{C}$



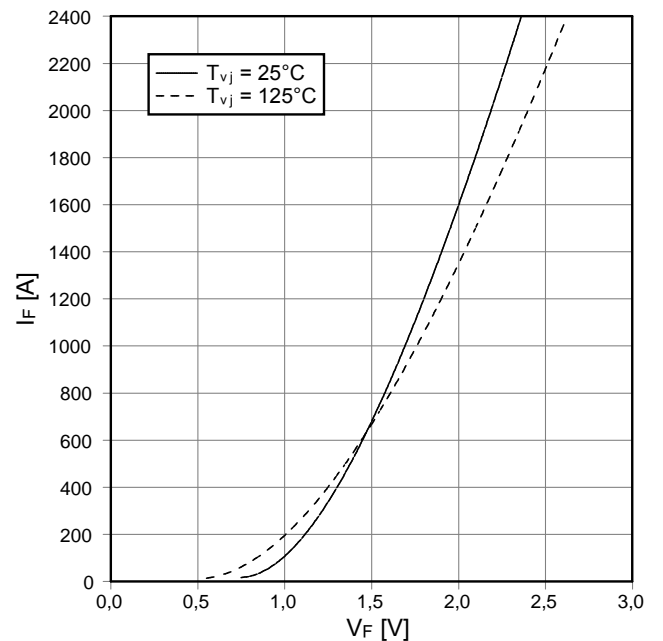
Transienter Wärmewiderstand IGBT-Wechsel.  
transient thermal impedance IGBT-inverter  
 $Z_{thJC} = f(t)$



Sicherer Rückwärts-Arbeitsbereich IGBT-Wr. (RBSOA)  
reverse bias safe operating area IGBT-inv. (RBSOA)  
 $I_C = f(V_{CE})$   
 $V_{GE} = \pm 15\text{ V}$ ,  $R_{Goff} = 1,5\ \Omega$ ,  $T_{vj} = 125^\circ\text{C}$



Durchlaßkennlinie der Diode-Wechsel. (typisch)  
forward characteristic of diode-inverter (typical)  
 $I_F = f(V_F)$



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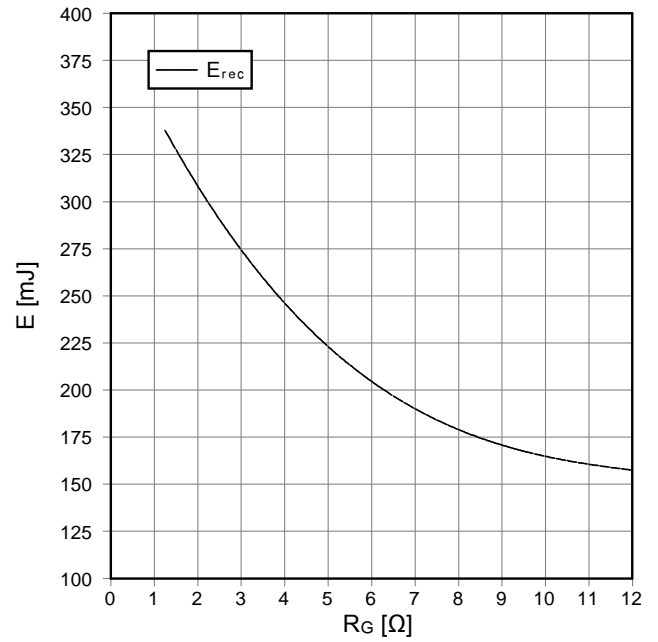
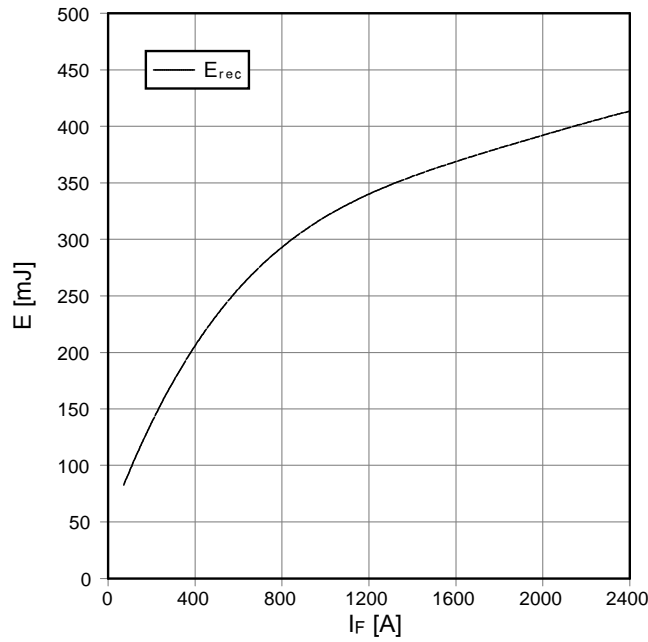
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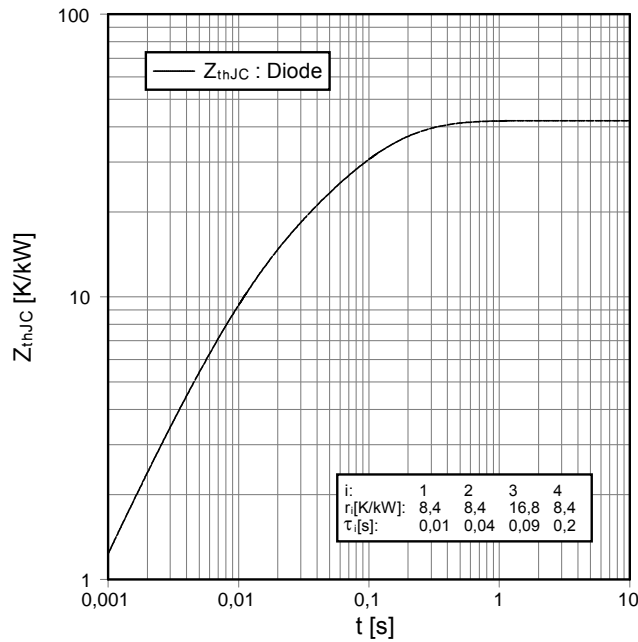
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Schaltverluste Diode-Wechselr. (typisch)  
switching losses diode-inverter (typical)  
 $E_{rec} = f(I_F)$   
 $R_{Gon} = 1,2 \Omega$ ,  $V_{CE} = 900 V$ ,  $T_{vj} = 125^\circ C$

Schaltverluste Diode-Wechselr. (typisch)  
switching losses diode-inverter (typical)  
 $E_{rec} = f(R_G)$   
 $I_F = 1200 A$ ,  $V_{CE} = 900 V$ ,  $T_{vj} = 125^\circ C$



Transienter Wärmewiderstand Diode-Wechselr.  
transient thermal impedance diode-inverter  
 $Z_{thJC} = f(t)$



i:	1	2	3	4
ri [K/kW]:	8,4	8,4	16,8	8,4
τi [s]:	0,01	0,04	0,09	0,2

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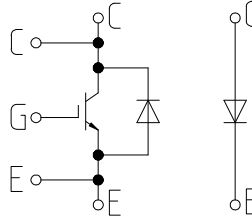
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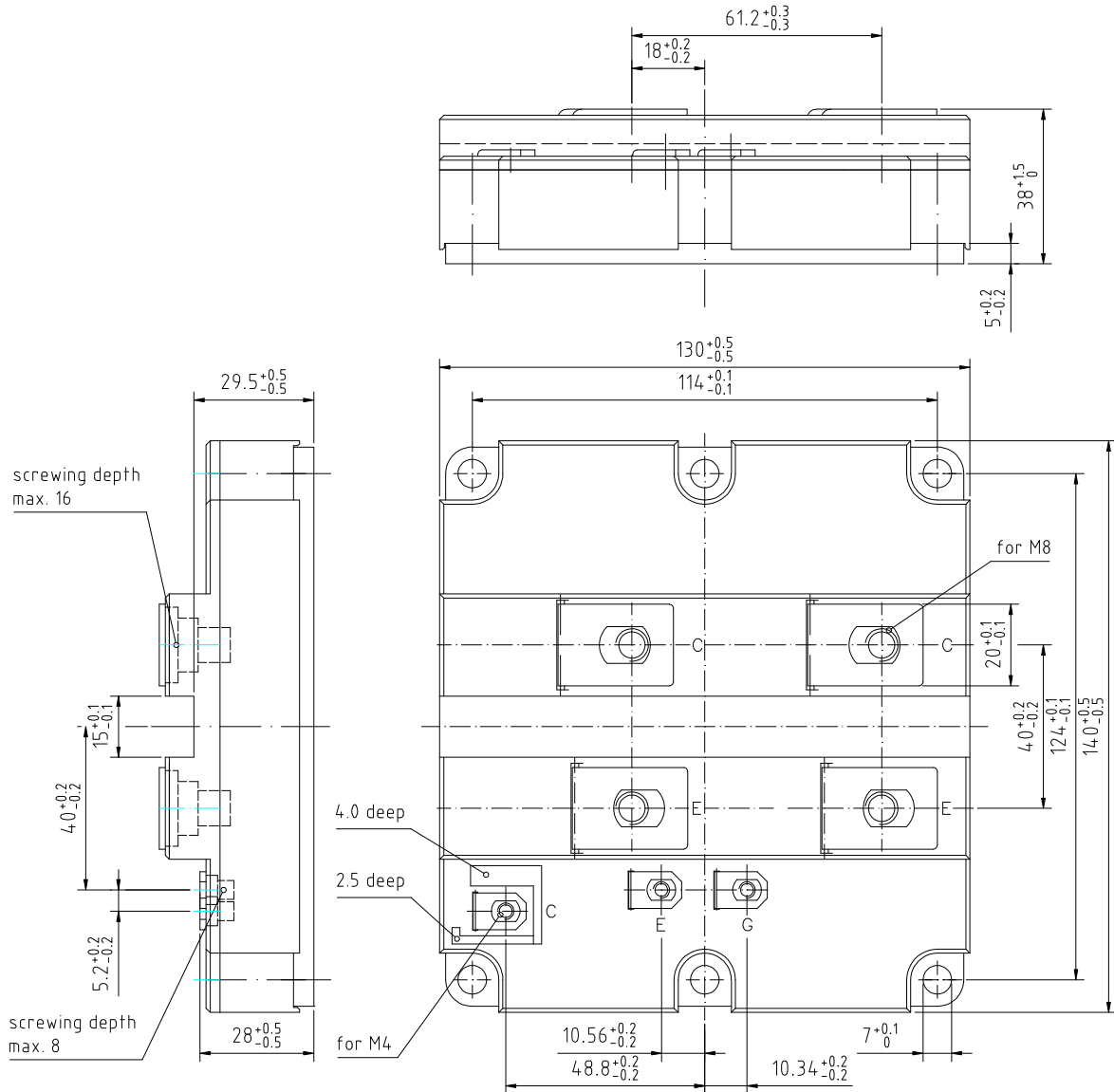


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Schaltplan / circuit diagram



Gehäuseabmessungen / package outlines



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